

100V N-CHANNEL ENHANCEMENT MODE MOSFET H-BRIDGE

Product Summary

BV _{DSS}	Rds(on) max	ID MAX TA = +25°C
100V	$33m\Omega$ @ V _{GS} = 10V	6A
	$50m\Omega @ V_{GS} = 4.5V$	5A

Description

This new generation complementary MOSFET H-Bridge features low on-resistance achievable with low gate drive.

Applications

- Motor Control
- DC-DC Converters
- Power Management

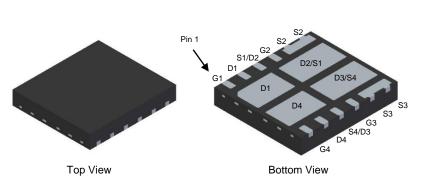
Features

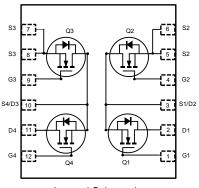
- Thermally Efficient Package Cooler Running Applications
- High Conversion Efficiency
- Low RDS(ON) Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: V-DFN5045-12
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (e4)
- Weight: 0.056 grams (Approximate)

V-DFN5045-12 (Type C)





Internal Schematic Top View

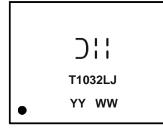
Ordering Information (Note 4)

Part Number	Case	Packaging
DMHT10H032LFJ-13	V-DFN5045-12 (Type C)	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



T1032LJ = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 20 = 2020)
WW = Week Code (01 to 53)



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			VDSS	100	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	lo	6 5	А		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	40	Α
Maximum Continuous Body Diode Forward Current (Note 6)			Is	2.5	Α
Pulsed Body Diode Current (10µs Pulse, Duty Cycle = 1%)			Ism	40	Α
Avalanche Current (Note 7) L = 0.3mH			las	13	Α
Avalanche Energy (Note 7) L = 0.3mH			Eas	25.3	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	130	°C/W
Total Power Dissipation (Note 6)		P_{D}	1.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	64	°C/W
Thermal Resistance, Junction to Case (Note 6)		Rejc	11	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

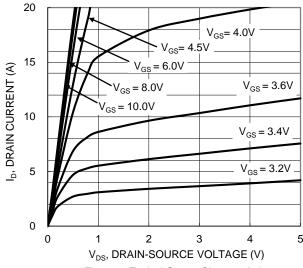
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

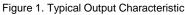
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BVDSS	100	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	$V_{DS} = 80V, V_{GS} = 0V$	
Gate-Source Leakage	Igss		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	1.3	_	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	0	_	25	33	mΩ	$V_{GS} = 10V, I_{D} = 6A$	
Static Drain-Source On-Resistance	RDS(ON)	_	34	50	11177	V _{GS} = 4.5V, I _D = 4A	
Diode Forward Voltage	VsD	_	0.8	1.0	V	V _G S = 0V, I _S = 6A	
DYNAMIC CHARACTERISTICS (Note 9)						•	
Input Capacitance	Ciss	l	683	l	рF		
Output Capacitance	Coss	-	165		pF	$V_{DS} = 50V, V_{GS} = 0V,$ - f = 1MHz	
Reverse Transfer Capacitance	Crss	_	6.9	_	pF	1 = 11/1112	
Gate Resistance	Rg	_	1.2	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_g	_	6.3	_	nC		
Total Gate Charge (V _{GS} = 10V)	Qg	_	11.9	_	nC	\/ F0\/ I- CA	
Gate-Source Charge	Qgs	_	2.0	_	nC	V _{DS} = 50V, I _D = 6A	
Gate-Drain Charge	Q_{gd}	_	3.1	_	nC	1	
Turn-On Delay Time	tD(ON)	_	4.1	_	ns		
Turn-On Rise Time	t _R	_	4.5	_	ns	$V_{DS} = 50V, R_{L} = 5.85\Omega$ $V_{GS} = 10V, R_{GEN} = 3\Omega$	
Turn-Off Delay Time	tD(OFF)	_	12.5	_	ns		
Turn-Off Fall Time	tF	_	9.3	_	ns		
Reverse Recovery Time	t _{RR}	_	31.5	_	ns	L CA 4:/44 500A/	
Reverse Recovery Charge	Q _{RR}		94.6	_	nC	I _F = 6A, di/dt = 500A/μs	

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
- 7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.







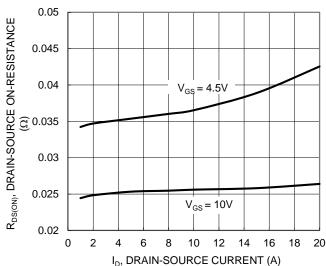


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

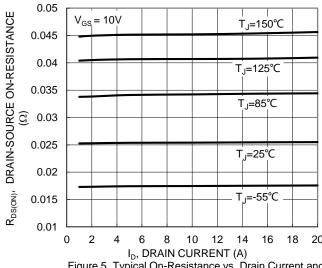


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

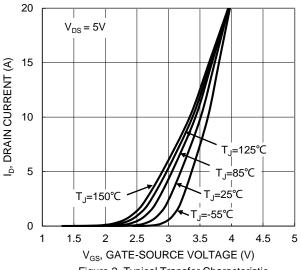


Figure 2. Typical Transfer Characteristic

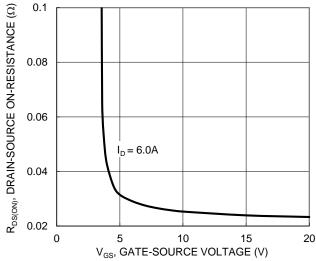


Figure 4. Typical Transfer Characteristic

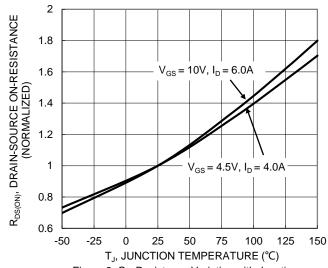


Figure 6. On-Resistance Variation with Junction Temperature



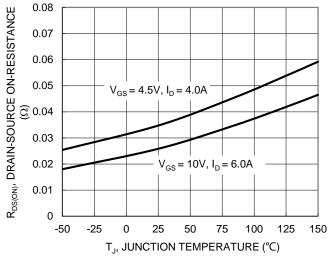
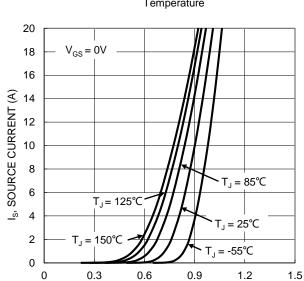


Figure 7. On-Resistance Variation with Junction Temperature



V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

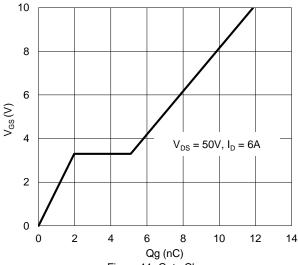


Figure 11. Gate Charge

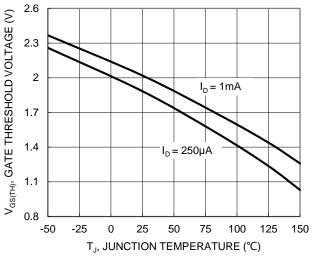
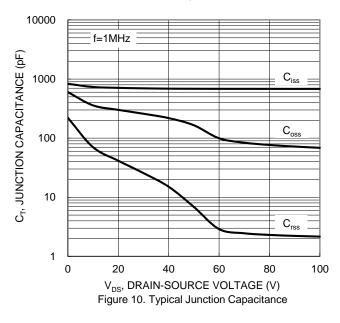
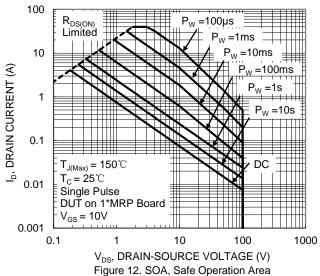


Figure 8. Gate Threshold Variation vs. Junction Temperature





June 2020

© Diodes Incorporated



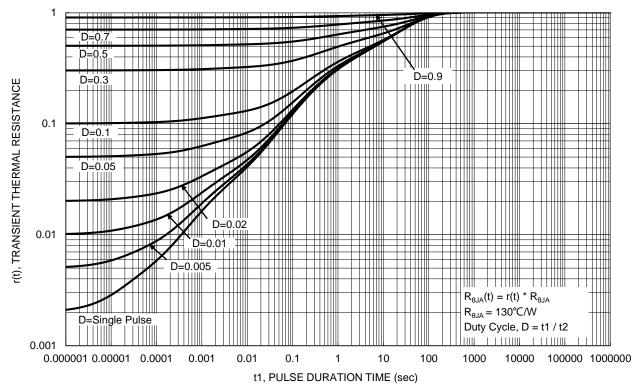


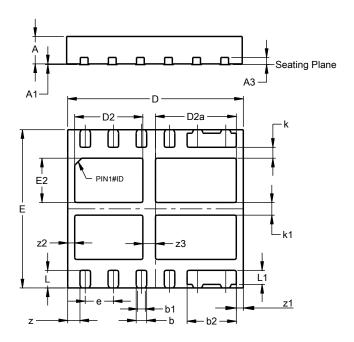
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

V-DFN5045-12 (Type C)

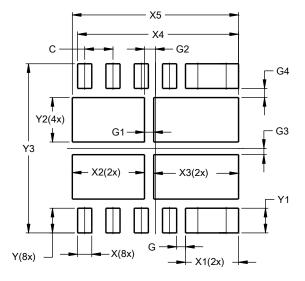


V-DFN5045-12 (Type C)				
Dim	Min	Тур		
Α	0.75	0.85	0.80	
A1	0.00	0.05	0.02	
A3	1		0.203	
b	0.25	0.35	0.30	
b1	0.17	0.27	0.22	
b2	1.35	1.45	1.40	
D	4.95	5.05	5.00	
D2	1.84	2.04	1.94	
D2a	2.20	2.40	2.30	
е	1		0.80	
Е	4.45	4.55	4.50	
E2	1.16	1.36	1.26	
k	-		0.31	
k1	1		0.36	
L	0.45	0.55	0.50	
L1	0.35	0.45	0.40	
Z	-		0.35	
z1	-		0.20	
z2	-		0.20	
z3			0.36	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

V-DFN5045-12 (Type C)



Dimensions	Value		
	(in mm)		
С	0.800		
G	0.250		
G1	0.260		
G2	0.310		
G3	0.180		
G4	0.260		
Х	0.400		
X1	1.500		
X2	2.040		
Х3	2.400		
X4	4.550		
X5	4.700		
Υ	0.700		
Y1	0.700		
Y2	1.260		
Y3	4.800		



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2020, Diodes Incorporated

www.diodes.com